

## Lehrstuhl für Physik

Department Physik, Mechanik und Elektrotechnik Montanuniversität Leoben



A-8700 LEOBEN, Franz Josef Straße 18, Austria Tel: +43 3842 402-4601 e-mail: physics@unileoben.ac.at

## S E M I N A R on Semiconductor Physics and Nanotechnology

Mo, 17.11.2025, 15:00 Uhr,

Seminar in person in the Physics lecture hall *or* via Zoom

## "Not-so-perfect 2D materials in vertical heterostructures and scalable devices"

Prof. Georg S. Duesberg

Institute of Physics, Faculty of Electrical Power Systems and Information Technology& SENS Research Center, University of the Bundeswehr Munich, Neubiberg, Germany

2D heterostructures are engineered materials that offer custom-tailored properties not found in nature. Despite significant progress in producing high-quality, small-scale van der Waals heterostructures through manual stacking by mechanical exfoliation and assembly, major challenges for scalability and reproducibility remain. To move beyond lab-scale experiments, there is a clear need for synthesis methods that are scalable, uniform, and reproducible.

This talk explores vertical heterostructures produced via scalable synthesis techniques such as chemical vapor deposition (CVD). Direct synthesis provides a promising route to exploiting the potential of these materials for next-generation electronics, optoelectronics, and sensing technologies.

Here, we present the growth and assembly of heterostructures and devices using highly controllable, industrial-scale methods. The grown 2D materials typically deviate from perfect crystallinity, exhibiting domain sizes ranging from a few nanometers to several micrometers. The chemical and morphological properties of the heterostacks were characterized using a range of complementary techniques, including energy-dispersive X-ray (EDX) spectroscopy, Raman spectroscopy, (angle-resolved) X-ray photoelectron spectroscopy (XPS), and time-of-flight secondary ion mass spectrometry (ToF-SIMS). In particular, the latter techniques elucidate the role of impurities in 2D materials. Finally, the electrical performance of devices based on these not-so-perfect 2D materials will be discussed.